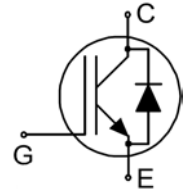


**IGBT chip with monolithically integrated diode in packages offering space saving advantage**
**Features:**

TRENCHSTOP™ Reverse Conducting (RC) technology for 600V applications offering:

- Optimised  $V_{CEsat}$  and  $V_F$  for low conduction losses
- Smooth switching performance leading to low EMI levels
- Very tight parameter distribution
- Operating range of 1 to 20kHz
- Maximum junction temperature 175°C
- Short circuit capability of 5µs
- Best in class current versus package size performance
- Qualified according to JEDEC for target applications
- Complete product spectrum and PSpice Models:

<http://www.infineon.com/igbt/>


**Applications:**

Motor drives

**Used for:**

Discrete components and molded modules

Chip Type	$V_{CE}$	$I_{Cn}$	Die Size	Package
IGC07R60D	600V	10A	2.65 x 2.68 mm <sup>2</sup>	sawn on foil

**Mechanical Parameter**

Raster size	2.65 x 2.68	mm <sup>2</sup>
Emitter pad size	see chip drawing	
Gate pad size	see chip drawing	
Area: total / active IGBT / active Diode	7.102 / 3.647 / 0.871	
Thickness	70	µm
Wafer size	150	mm
Max.possible chips per wafer	2069	
Passivation frontside	Photoimide	
Pad metal	3200 nm AlSiCu	
Backside metal	Ni Ag –system suitable for epoxy and soft solder die bonding	
Die bond	Electrically conductive glue or solder	
Wire bond	Al, <500µm	
Reject ink dot size	Ø 0.65mm ; max 1.2mm	
Recommended storage environment	Store in original container, in dry nitrogen, in dark environment, < 6 month at an ambient temperature of 23°C	

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Collector-Emitter voltage, $T_j=25\text{ °C}$	$V_{CE}$	600	V
DC collector current, limited by $T_{j\max}$	$I_C$	1)	A
Pulsed collector current, $t_p$ limited by $T_{j\max}$	$I_{C,puls}$	30	A
Gate emitter voltage	$V_{GE}$	±20	V
Junction temperature	$T_{vj,max}$	-40 .. +175	°C
Operating junction temperature	$T_{vj,op,max}$	-40 .. +175	°C
Short circuit data <sup>2)</sup> $V_{GE} = 15V, V_{CC} = 400V, T_{vj} = 150\text{ °C}$	$t_{p,max}$	5	µs
Safe operating area IGBT <sup>2)3)</sup>	$I_{C,max} = 20A, V_{CE,max} = 600V, T_{vj,op} \leq T_{vj,op,max}$		
Safe operating area Diode <sup>2)</sup>	$I_{F,max} = 20A, V_{R,max} = 600V,$ $P_{max} = 8\text{ kW}, T_{vj,op} \leq T_{vj,op,max}$		

1) depending on thermal properties of assembly

2) not subject to production test - verified by design/characterization

3) allowed number of short circuits: <1000; time between short circuits: >1s

**Static Characteristics (tested on wafer),  $T_j=25\text{ °C}$** 

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Collector-Emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=0.2mA$	600			V
Collector-Emitter saturation voltage	$V_{CE(sat)}$	$V_{GE}=15V, I_C=10A$		1.65	2.1	
Diode Forward Voltage	$V_F$	$V_{GE}=0V, I_F=10A$		1.7	2.1	
Gate-Emitter threshold voltage	$V_{GE(th)}$	$I_C=0.17mA, V_{GE}=V_{CE}$	4.3	5	5.7	
Zero gate voltage collector current	$I_{CES}$	$V_{CE}=600V, V_{GE}=0V$			40	µA
Gate-Emitter leakage current	$I_{GES}$	$V_{CE}=0V, V_{GE}=20V$			100	nA
Integrated gate resistor	$R_{Gint}$			0		Ω

**Dynamic Characteristics (not subject to production test - verified by design / characterization),  $T_j=25\text{ °C}$** 

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Input capacitance	$C_{iss}$	$V_{CE}=25V,$ $V_{GE}=0V,$ $f=1MHz$		655		pF
Output capacitance	$C_{oss}$			37		
Reverse transfer capacitance	$C_{riss}$			22		



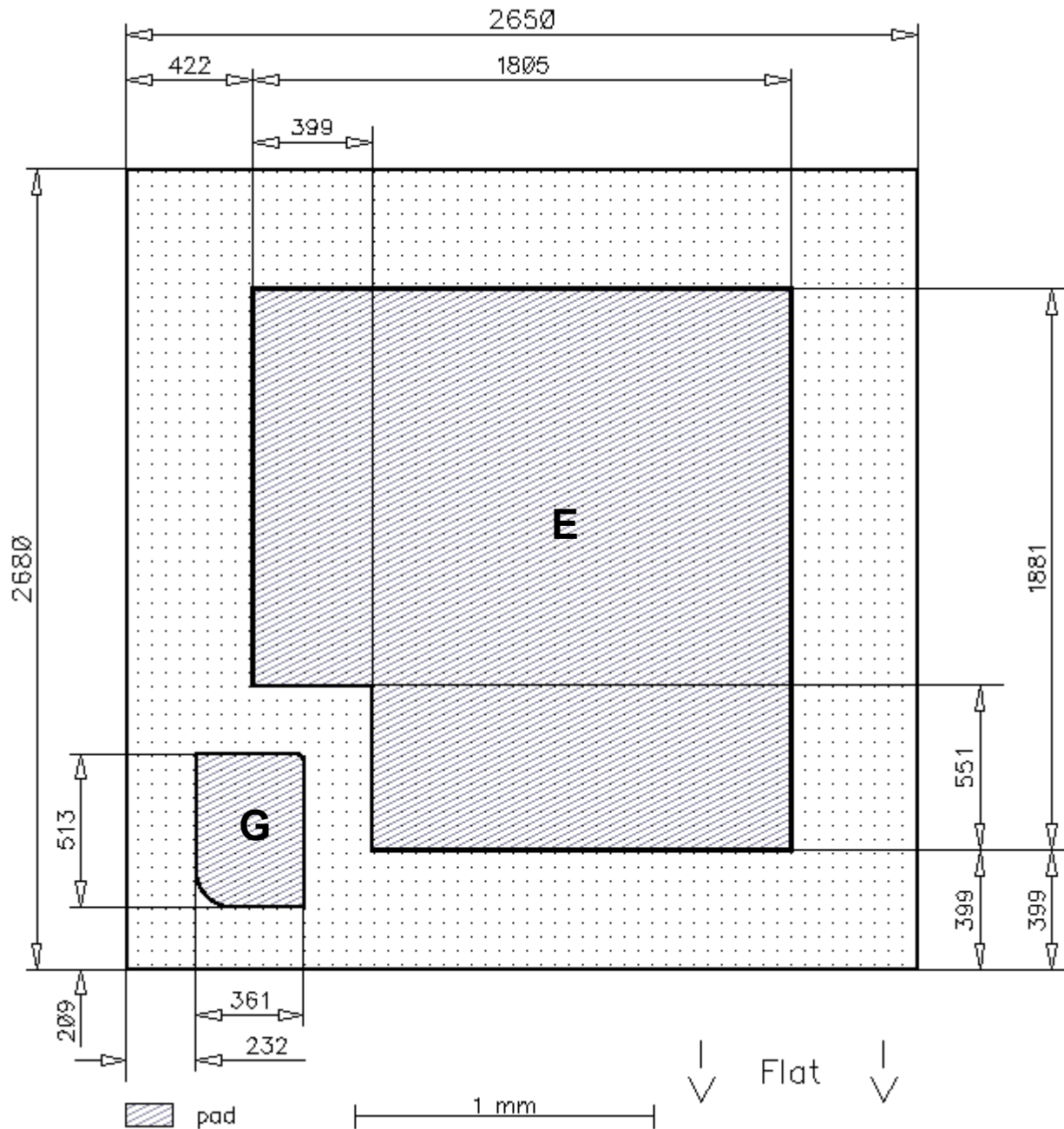
### **Further Electrical Characteristic**

Switching characteristics and thermal properties are depending strongly on package design and mounting technology and can therefore not be specified for a bare die.

Further technical information about the performance of this chip in package t.b.d. is given exemplarily at [www.infineon.com/igbt](http://www.infineon.com/igbt). The chip qualification is independent of the qualification which is performed for the Discretes.

Chip Drawing

Die-Size 2650 μm x 2680 μm

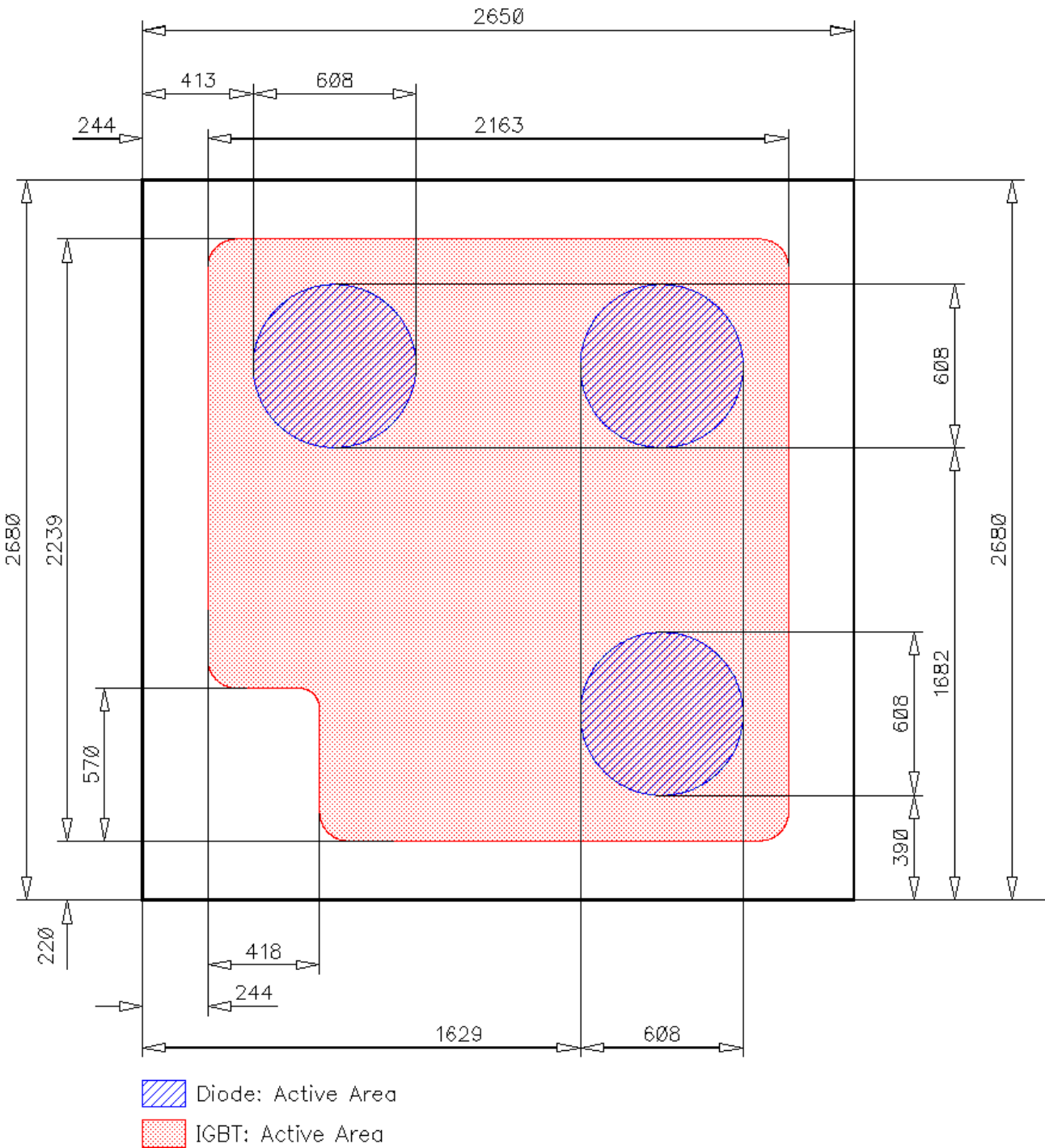


**E** = Emitter  
**G** = Gate

Chip Drawing active areas

Die-Size 2650 um x 2680 um

L7385



**Description**

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AQL 0,65 for visual inspection according to failure catalogue

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Electrostatic Discharge Sensitive Device according to MIL-STD 883

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**Revision History**

Version	Subjects (major changes since last revision)	Date
2.0	Release of final datasheet	12.01.2010

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